



Data sheet acquired from Harris Semiconductor
SCHS021

CD4011B, CD4012B, CD4023B Types

CMOS NAND GATES

High-Voltage Types (20-Volt Rating)

Quad 2 Input — CD4011B
Dual 4 Input — CD4012B
Triple 3 Input — CD4023B

■ CD4011B, CD4012B, and CD4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

The CD4011B, CD4012B, and CD4023B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

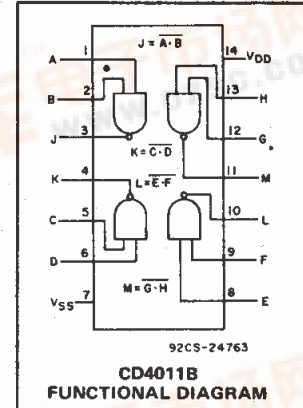
- Propagation delay time = 60 ns (typ.) at $C_L = 50$ pF, $V_{DD} = 10$ V
- Buffered inputs and outputs
- Standardized symmetrical output characteristics
- Maximum input current of $1 \mu A$ at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin (over full package temperature range):

1 V at $V_{DD} = 5$ V

2 V at $V_{DD} = 10$ V

2.5 V at $V_{DD} = 15$ V

- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of "B" Series CMOS Devices"



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5$ V

DC INPUT CURRENT, ANY ONE INPUT ± 10 mA

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500 mW

For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$ Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

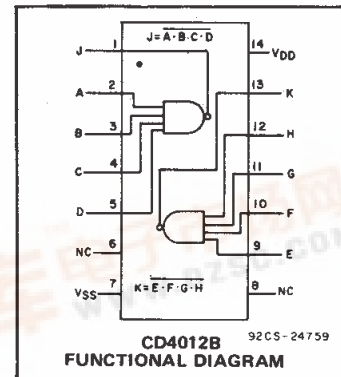
For $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100 mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$

STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10 s max $+265^\circ\text{C}$

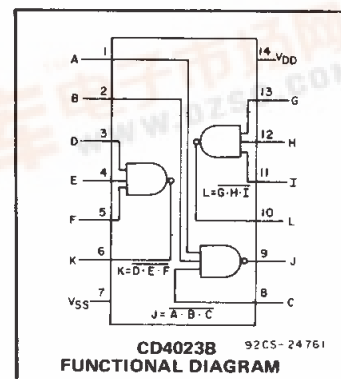
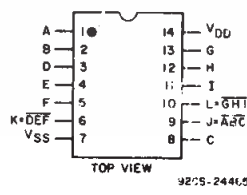
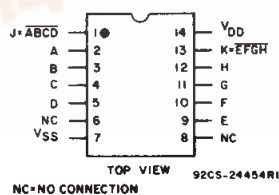
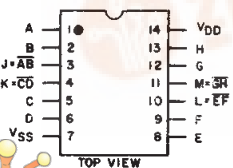


RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A = \text{Full Package Temperature Range}$)	3	18	V

TERMINAL ASSIGNMENTS



CD4011B, CD4012B, CD4023B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)					+25			
				-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0,5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0,10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0,15	15	1	1	30	30	—	0.01	1	
	—	0,20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	4.5	—	5	1.5				—	—	1.5	V
	9	—	10	3				—	—	3	
	13.5	—	15	4				—	—	4	
Input High Voltage, V _{IH} Min.	0.5,4.5	—	5	3.5				3.5	—	—	V
	1,9	—	10	7				7	—	—	
	1.5,13.5	—	15	11				11	—	—	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA

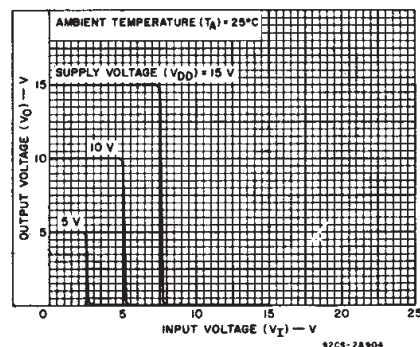


Fig. 1 — Typical voltage transfer characteristics.

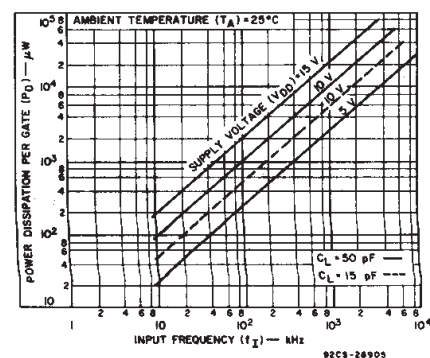


Fig. 2 — Typical power dissipation characteristics.

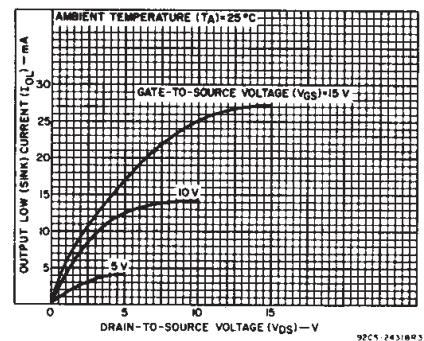


Fig. 3 — Typical output low (sink) current characteristics.

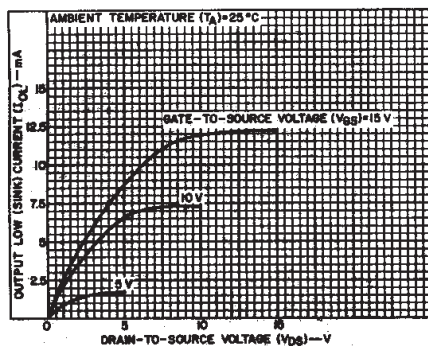


Fig. 4 — Minimum output low (sink) current characteristics.

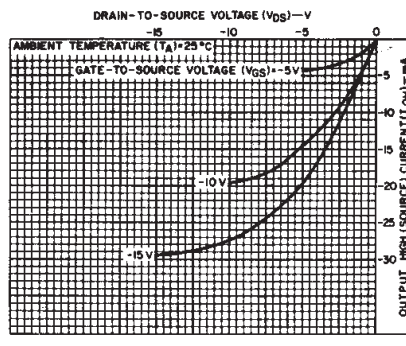


Fig. 5 — Typical output high (source) current characteristics.

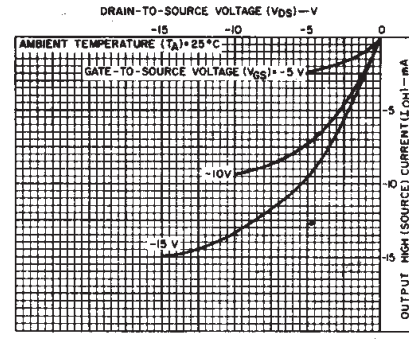
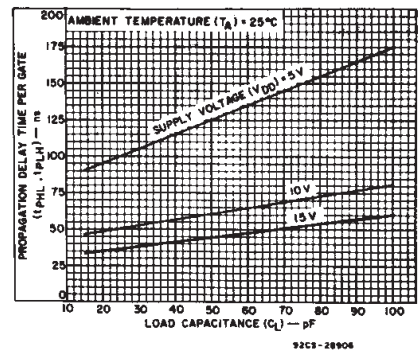
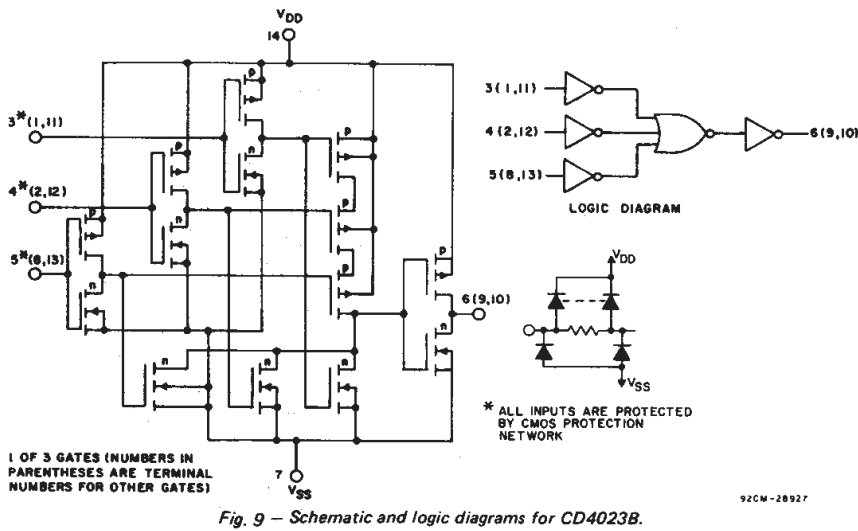
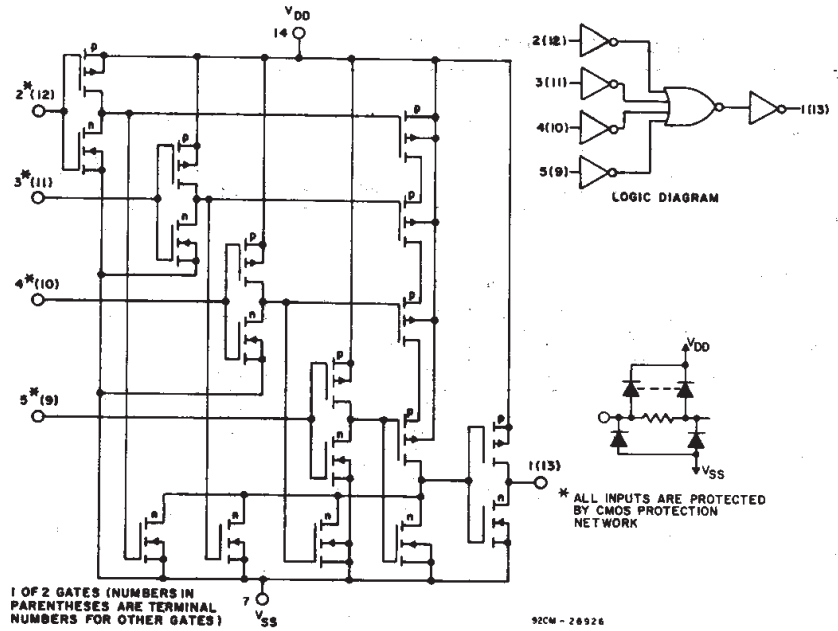
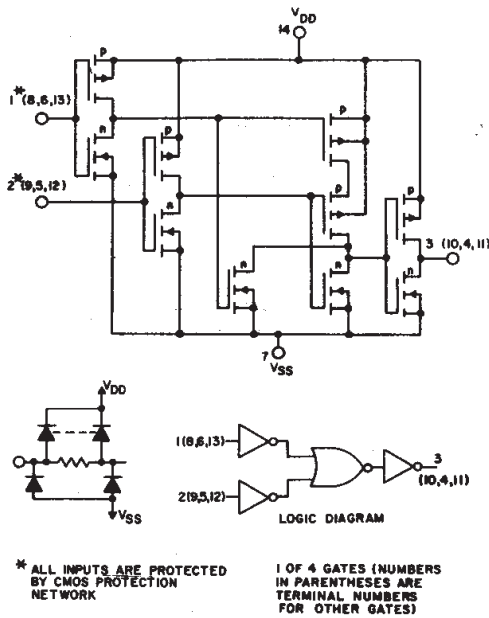


Fig. 6 — Minimum output high (source) current characteristics.

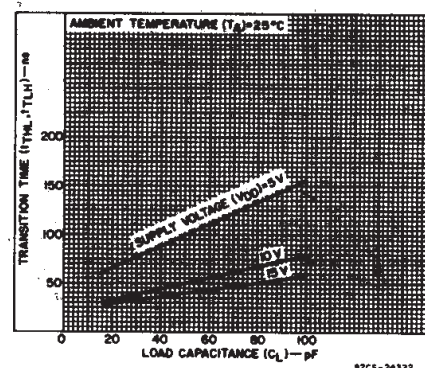
CD4011B, CD4012B, CD4023B Types



DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS
		V_{DD} VOLTS	TYP.	MAX.
Propagation Delay Time, t_{PHL}, t_{PLH}		5	125	250
		10	60	120
		15	45	90
Transition Time, t_{THL}, t_{TLH}		5	100	200
		10	50	100
		15	40	80
Input Capacitance, C_{IN}	Any Input		5	7.5
				pF



CD4011B, CD4012B, CD4023B Types

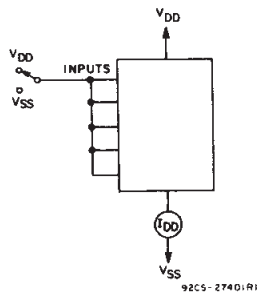


Fig. 12 - Quiescent-device-current test circuit.

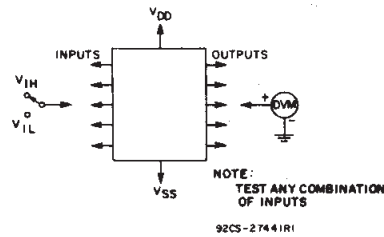


Fig. 13 - Input-voltage test circuit.

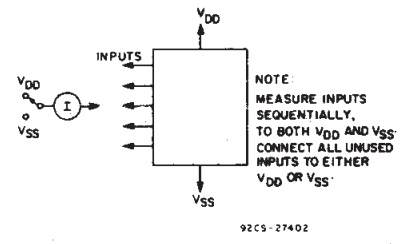
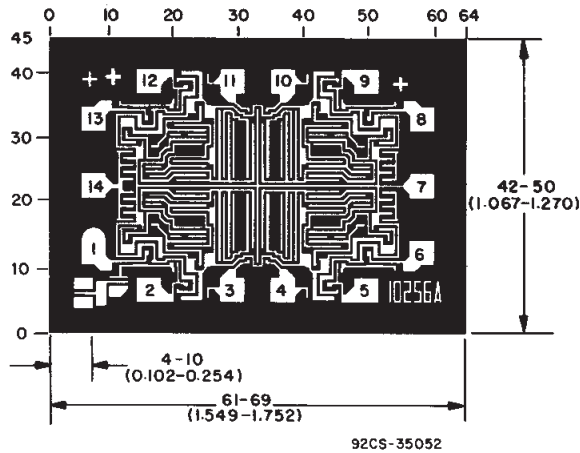
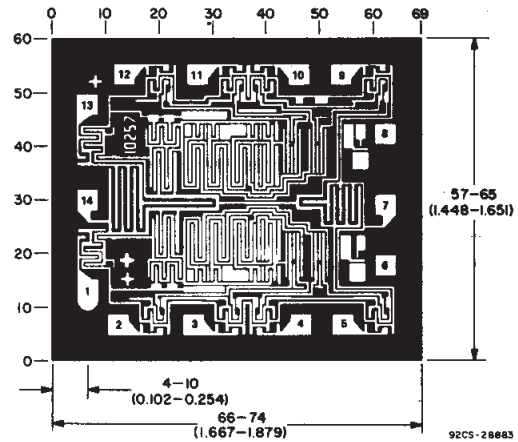


Fig. 14 - Input-current test circuit.

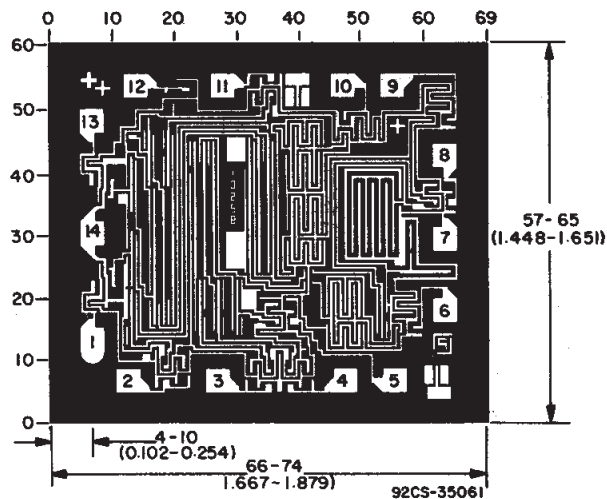
Chip Dimensions and Pad Layouts



CD4011BH



CD4012BH



CD4023BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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